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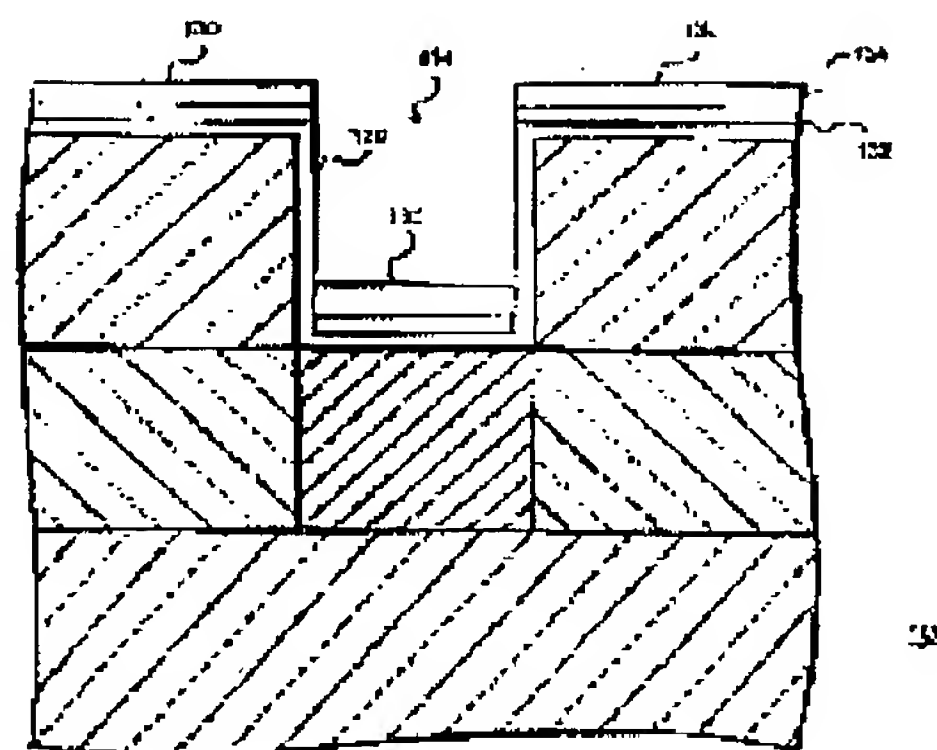
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(54) RESISTOR AND ITS MANUFACTURE

(57)Abstract:

PROBLEM TO BE SOLVED: To manufacture a high resistance resistor by using materials and a method common the those used for the integrated circuit process.

SOLUTION: As a method for manufacturing a resistor element for an integrated circuit semiconductor device, and insulation film 120 formed is silicon nitride and the like is deposited first. Then, a film 130 containing titanium is deposited on the insulation film 120. The film 130 and the insulation film 120 are heat-treated so as the diffuse titanium in the insulation film 120. As a result, titanium is diffused in the insulation film 120. Thus, a resistor element with relatively high resistance is manufactured. The merit of this method is that it can be easily integrated with the conventional integrated circuit manufacturing technologies.



LEGAL STATUS

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